

# Field Stop Trench IGBT

## 650 V, 75 A

### FGHL75T65MQDT

Field stop 4<sup>th</sup> generation mid speed IGBT technology copacked with full rated current diode.

#### Features

- Maximum Junction Temperature:  $T_J = 175^\circ\text{C}$
- Positive Temperature Co-efficient for Easy Parallel Operating
- High Current Capability
- Low Saturation Voltage:  $V_{CE(Sat)} = 1.45\text{ V (Typ.) @ } I_C = 75\text{ A}$
- 100% of the Parts are Tested for  $I_{LM}$  (Note 2)
- Smooth and Optimized Switching
- Tight Parameter Distribution
- RoHS Compliant

#### Typical Applications

- Solar Inverter
- UPS, ESS
- PFC, Converters

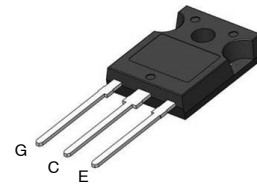
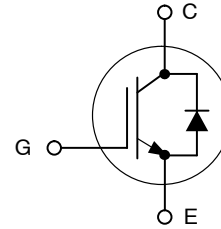
#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-to-Emitter Voltage	$V_{CES}$	650	V
Gate-to-Emitter Voltage Transient Gate-to-Emitter Voltage	$V_{GES}$	$\pm 20$ $\pm 30$	V
Collector Current (Note 1) @ $T_C = 25^\circ\text{C}$ @ $T_C = 100^\circ\text{C}$	$I_C$	80 75	A
Pulsed Collector Current (Note 2)	$I_{LM}$	300	A
Pulsed Collector Current (Note 3)	$I_{CM}$	300	A
Diode Forward Current (Note 1) @ $T_C = 25^\circ\text{C}$ @ $T_C = 100^\circ\text{C}$	$I_F$	80 75	A
Pulsed Diode Maximum Forward Current	$I_{FM}$	300	A
Maximum Power Dissipation @ $T_C = 25^\circ\text{C}$ @ $T_C = 100^\circ\text{C}$	$P_D$	375 188	W
Operating Junction and Storage Temperature Range	$T_J, T_{STG}$	-55 to +175	$^\circ\text{C}$
Maximum Lead Temp. for Soldering Purposes (1/8" from case for 5 s)	$T_L$	260	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Value limit by bond wire
2.  $V_{CC} = 400\text{ V}, V_{GE} = 15\text{ V}, I_C = 300\text{ A}, R_G = 9\ \Omega$ , Inductive Load, 100% tested
3. Repetitive rating: pulse width limited by max. junction temperature

75 A, 650 V  
 $V_{CESat} = 1.45\text{ V}$



TO-247-3L  
CASE 340CX

#### MARKING DIAGRAM



- &Y = ON Semiconductor Logo
- &Z = Assembly Plant Code
- &3 = 3-Digit Date Code
- &K = 2-Digit Lot Traceability Code
- FGHL75T65MQDT = Specific Device Code

#### ORDERING INFORMATION

Device	Package	Shipping
FGHL75T65MQDT	TO-247-3L	30 Units / Tube

# FGHL75T65MQDT

## THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Thermal resistance junction-to-case, for IGBT	$R_{\theta JC}$	0.40	$^{\circ}\text{C}/\text{W}$
Thermal resistance junction-to-case, for Diode	$R_{\theta JC}$	0.60	$^{\circ}\text{C}/\text{W}$
Thermal resistance junction-to-ambient	$R_{\theta JA}$	40	$^{\circ}\text{C}/\text{W}$

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
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### OFF CHARACTERISTICS

Collector-emitter breakdown voltage, gate-emitter short-circuited	$V_{GE} = 0\text{ V},$ $I_C = 1\text{ mA}$	$BV_{CES}$	650	-	-	V
Temperature Coefficient of Breakdown Voltage	$V_{GE} = 0\text{ V},$ $I_C = 1\text{ mA}$	$\frac{\Delta BV_{CES}}{\Delta T_J}$	-	0.6	-	$\text{V}/^{\circ}\text{C}$
Collector-emitter cut-off current, gate-emitter short-circuited	$V_{GE} = 0\text{ V},$ $V_{CE} = 650\text{ V}$	$I_{CES}$	-	-	250	$\mu\text{A}$
Gate leakage current, collector-emitter short-circuited	$V_{GE} = 20\text{ V},$ $V_{CE} = 0\text{ V}$	$I_{GES}$	-	-	$\pm 400$	nA

### ON CHARACTERISTICS

Gate-emitter threshold voltage	$V_{GE} = V_{CE}, I_C = 75\text{ mA}$	$V_{GE(th)}$	3.0	4.5	6.0	V
Collector-emitter saturation voltage	$V_{GE} = 15\text{ V}, I_C = 75\text{ A}, T_J = 25^{\circ}\text{C}$ $V_{GE} = 15\text{ V}, I_C = 75\text{ A}, T_J = 150^{\circ}\text{C}$	$V_{CE(sat)}$	-	1.45	1.8	V
			-	1.65	-	

### DYNAMIC CHARACTERISTICS

Input capacitance	$V_{CE} = 30\text{ V},$ $V_{GE} = 0\text{ V},$ $f = 1\text{ MHz}$	$C_{ies}$	-	4954	-	$\mu\text{F}$
Output capacitance		$C_{oes}$	-	163	-	
Reverse transfer capacitance		$C_{res}$	-	14	-	
Gate charge total	$V_{CE} = 400\text{ V},$ $I_C = 75\text{ A},$ $V_{GE} = 15\text{ V}$	$Q_g$	-	149	-	nC
Gate-to-emitter charge		$Q_{ge}$	-	27	-	
Gate-to-collector charge		$Q_{gc}$	-	34	-	

### SWITCHING CHARACTERISTICS, INDUCTIVE LOAD

Turn-on delay time	$T_C = 25^{\circ}\text{C},$ $V_{CC} = 400\text{ V},$ $I_C = 37.5\text{ A},$ $R_G = 4.7\ \Omega,$ $V_{GE} = 15\text{ V},$ Inductive Load	$t_{d(on)}$	-	22	-	ns	
Rise time		$t_r$	-	21	-		
Turn-off delay time		$t_{d(off)}$	-	125	-		
Fall time			$t_f$	-	11	-	mJ
Turn-on switching loss		$E_{on}$	-	0.86	-		
Turn-off switching loss		$E_{off}$	-	0.49	-		
Total switching loss		$E_{ts}$	-	1.35	-		
Turn-on delay time	$T_C = 25^{\circ}\text{C},$ $V_{CC} = 400\text{ V},$ $I_C = 75\text{ A},$ $R_G = 4.7\ \Omega,$ $V_{GE} = 15\text{ V},$ Inductive Load	$t_{d(on)}$	-	24	-	ns	
Rise time		$t_r$	-	46	-		
Turn-off delay time		$t_{d(off)}$	-	118	-		
Fall time			$t_f$	-	66	-	mJ
Turn-on switching loss		$E_{on}$	-	2.35	-		
Turn-off switching loss		$E_{off}$	-	1.25	-		
Total switching loss		$E_{ts}$	-	3.6	-		

# FGHL75T65MQDT

## ELECTRICAL CHARACTERISTICS ( $T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Test Conditions	Symbol	Min	Typ	Max	Unit
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### SWITCHING CHARACTERISTICS, INDUCTIVE LOAD

Turn-on delay time	$T_C = 150^\circ\text{C}$ , $V_{CC} = 400\text{ V}$ , $I_C = 37.5\text{ A}$ , $R_G = 4.7\ \Omega$ , $V_{GE} = 15\text{ V}$ , Inductive Load	$t_{d(on)}$	-	22	-	ns
Rise time		$t_r$	-	22	-	
Turn-off delay time		$t_{d(off)}$	-	142	-	
Fall time		$t_f$	-	85	-	
Turn-on switching loss		$E_{on}$	-	1.43	-	mJ
Turn-off switching loss		$E_{off}$	-	0.85	-	
Total switching loss		$E_{ts}$	-	2.28	-	
Turn-on delay time		$T_C = 150^\circ\text{C}$ , $V_{CC} = 400\text{ V}$ , $I_C = 75\text{ A}$ , $R_G = 4.7\ \Omega$ , $V_{GE} = 15\text{ V}$ , Inductive Load	$t_{d(on)}$	-	24	-
Rise time	$t_r$		-	50	-	
Turn-off delay time	$t_{d(off)}$		-	126	-	
Fall time	$t_f$		-	80	-	
Turn-on switching loss	$E_{on}$		-	3.24	-	mJ
Turn-off switching loss	$E_{off}$		-	1.75	-	
Total switching loss	$E_{ts}$		-	4.99	-	

### DIODE CHARACTERISTICS

Diode Forward Voltage	$I_F = 75\text{ A}$ , $T_J = 25^\circ\text{C}$	$V_{FM}$	-	1.65	2.1	V
	$I_F = 75\text{ A}$ , $T_J = 150^\circ\text{C}$		-	1.55	-	

### DIODE SWITCHING CHARACTERISTICS, INDUCTIVE LOAD

Reverse Recovery Energy	$T_C = 25^\circ\text{C}$ , $V_{CE} = 400\text{ V}$ , $I_F = 37.5\text{ A}$ , $di_F/dt = 1000\text{ A}/\mu\text{s}$	$E_{rec}$	-	105	-	$\mu\text{J}$
Diode Reverse Recovery Time		$T_{rr}$	-	58	-	ns
Diode Reverse Recovery Charge		$Q_{rr}$	-	591	-	nC
Reverse Recovery Energy	$T_C = 25^\circ\text{C}$ , $V_{CE} = 400\text{ V}$ , $I_F = 75\text{ A}$ , $di_F/dt = 1000\text{ A}/\mu\text{s}$	$E_{rec}$	-	235	-	$\mu\text{J}$
Diode Reverse Recovery Time		$T_{rr}$	-	107	-	ns
Diode Reverse Recovery Charge		$Q_{rr}$	-	1113	-	nC
Reverse Recovery Energy	$T_C = 150^\circ\text{C}$ , $V_{CE} = 400\text{ V}$ , $I_F = 37.5\text{ A}$ , $di_F/dt = 1000\text{ A}/\mu\text{s}$	$E_{rec}$	-	747	-	$\mu\text{J}$
Diode Reverse Recovery Time		$T_{rr}$	-	151	-	ns
Diode Reverse Recovery Charge		$Q_{rr}$	-	2780	-	nC
Reverse Recovery Energy	$T_C = 150^\circ\text{C}$ , $V_{CE} = 400\text{ V}$ , $I_F = 75\text{ A}$ , $di_F/dt = 1000\text{ A}/\mu\text{s}$	$E_{rec}$	-	865	-	$\mu\text{J}$
Diode Reverse Recovery Time		$T_{rr}$	-	171	-	ns
Diode Reverse Recovery Charge		$Q_{rr}$	-	3286	-	nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

# FGHL75T65MQDT

## TYPICAL CHARACTERISTICS

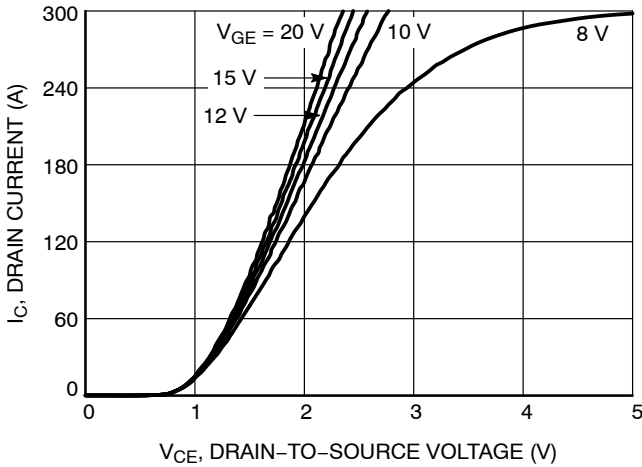


Figure 1. Typical Output Characteristics (25°C)

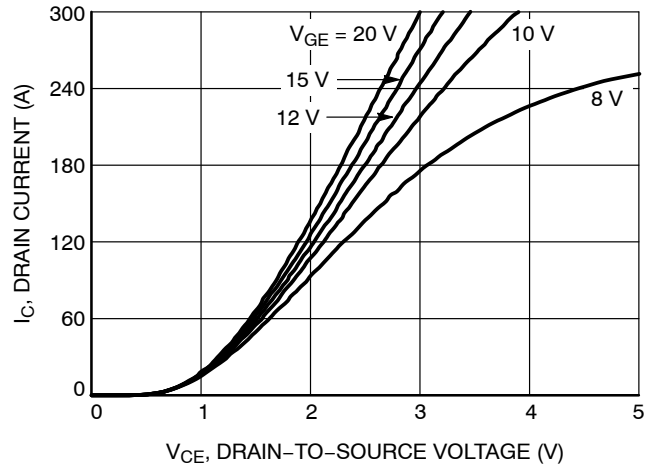


Figure 2. Typical Output Characteristics (150°C)

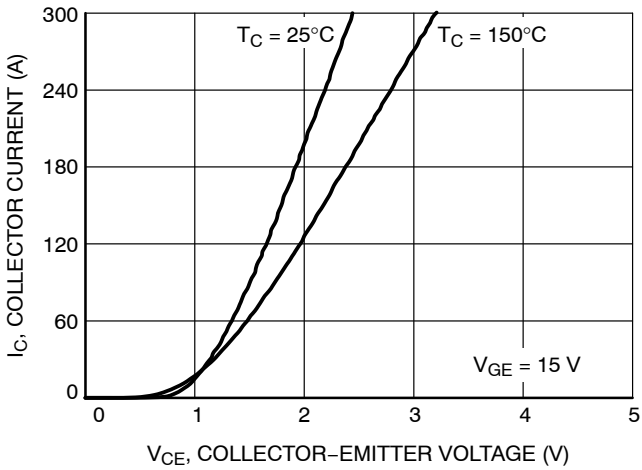


Figure 3. Typical Saturation Voltage Characteristics

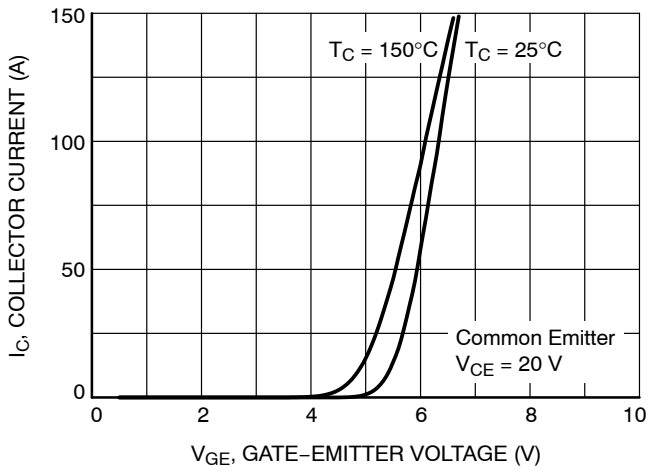


Figure 4. Typical Transfer Characteristics

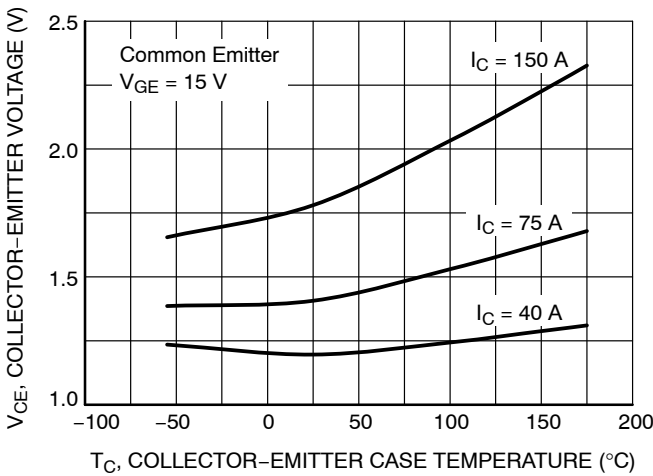


Figure 5. Saturation Voltage vs. Case Temperature

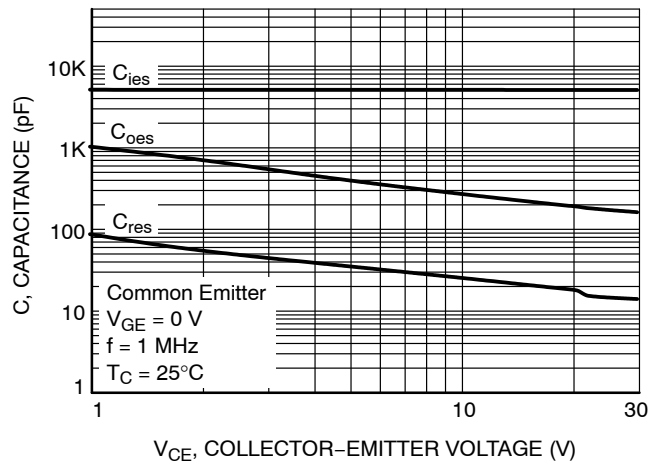


Figure 6. Capacitance Characteristics

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## TYPICAL CHARACTERISTICS

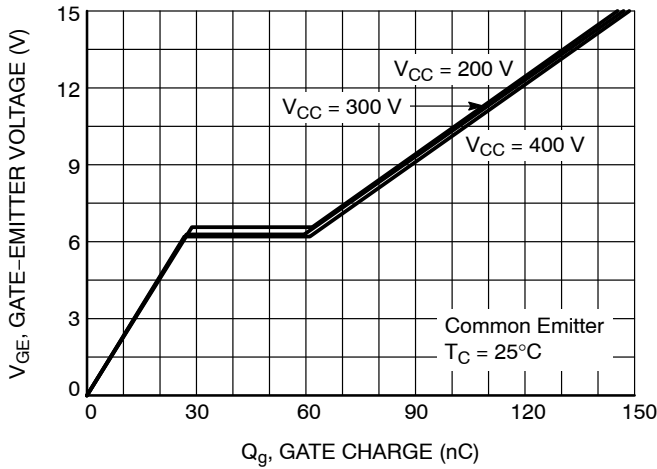


Figure 7. Gate Charge Characteristics

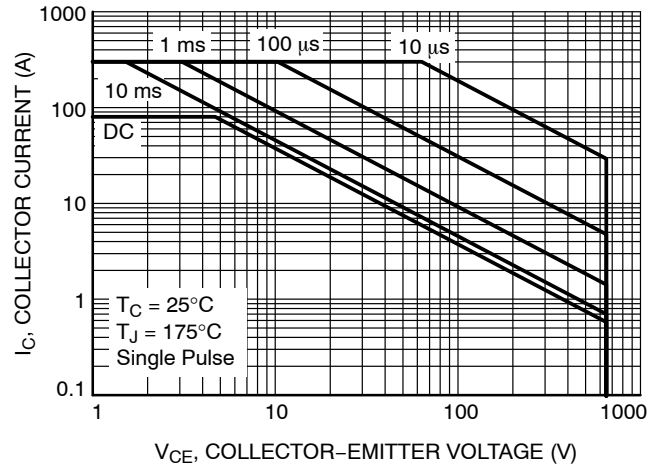


Figure 8. SOA Characteristics

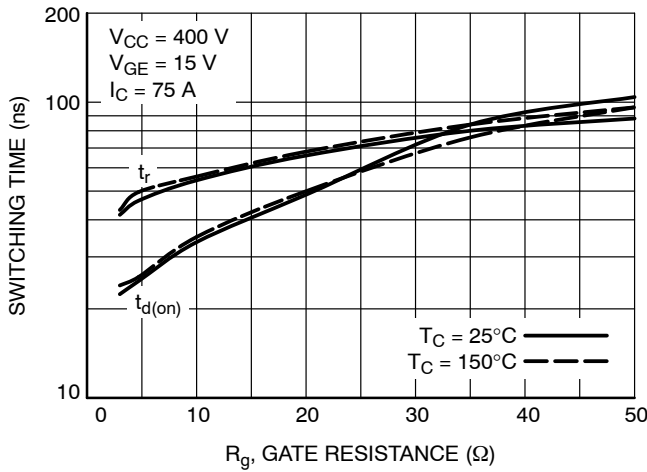


Figure 9. Turn-On Characteristics vs. Gate Resistance

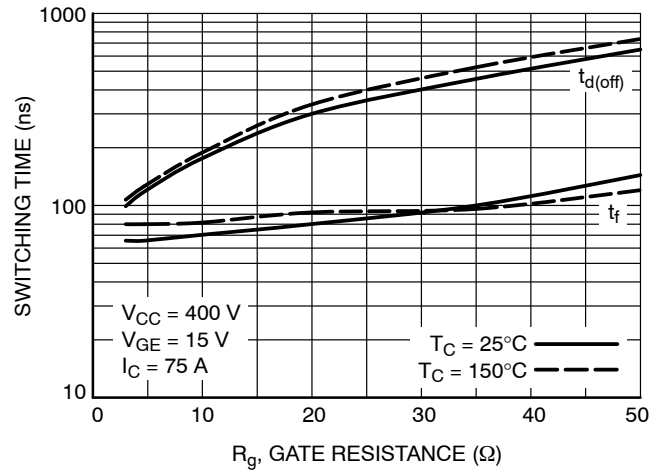


Figure 10. Turn-Off Characteristics vs. Gate Resistance

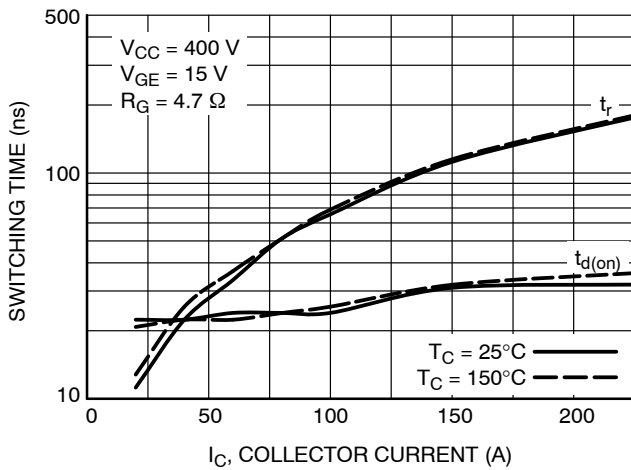


Figure 11. Turn-On Characteristics vs. Collector Current

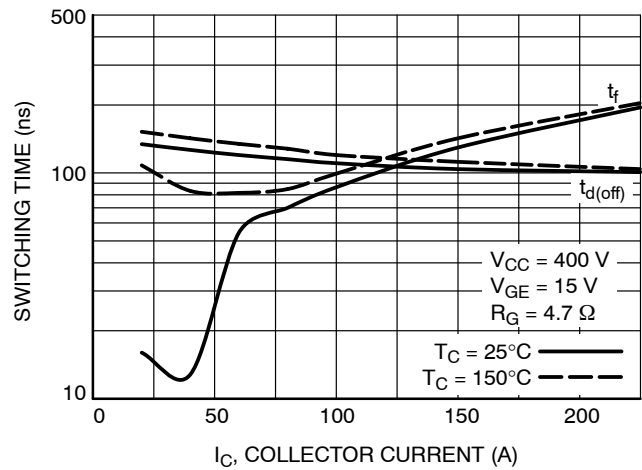


Figure 12. Turn-Off Characteristics vs. Collector Current

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## TYPICAL CHARACTERISTICS

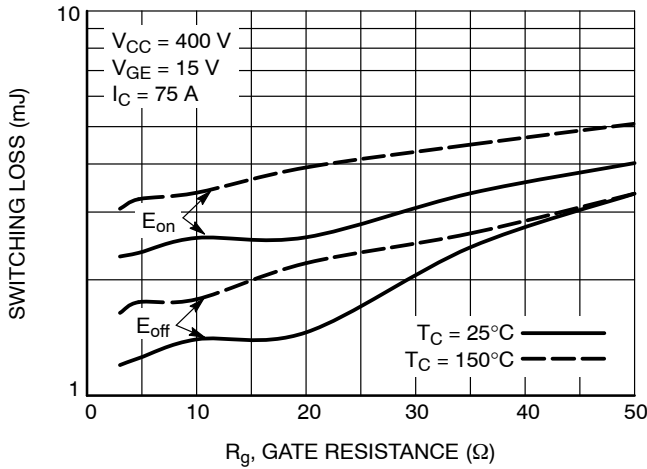


Figure 13. Switching Loss vs. Gate Resistance

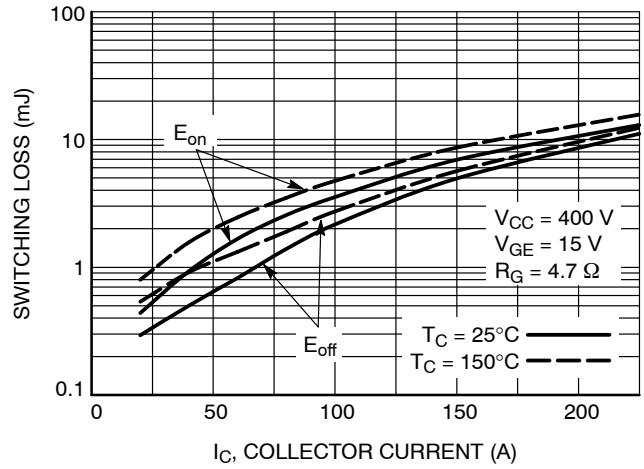


Figure 14. Switching Loss vs. Collector Current

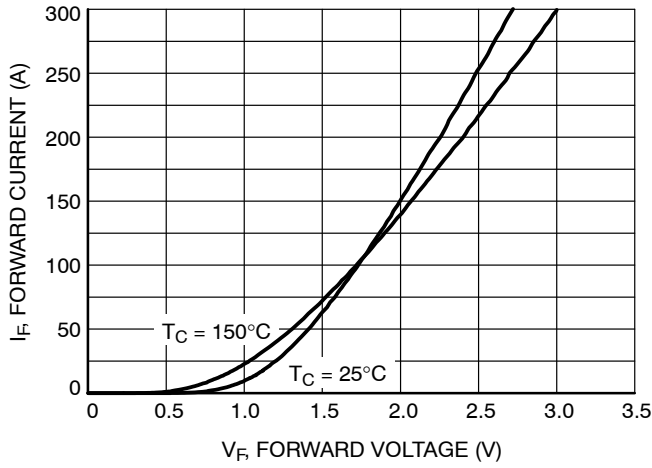


Figure 15. Forward Characteristics

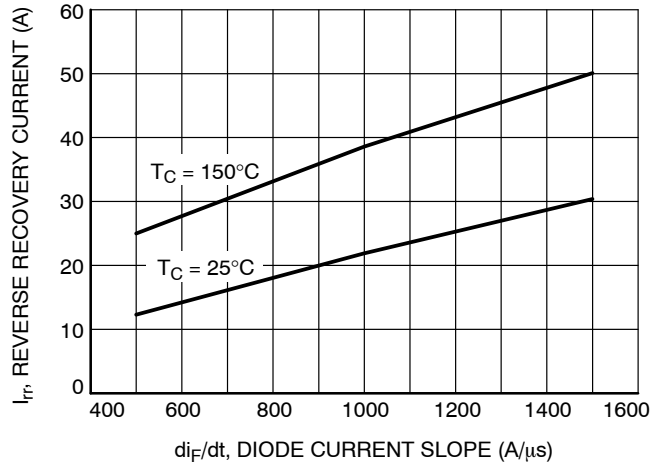


Figure 16. Reverse Recovery Current

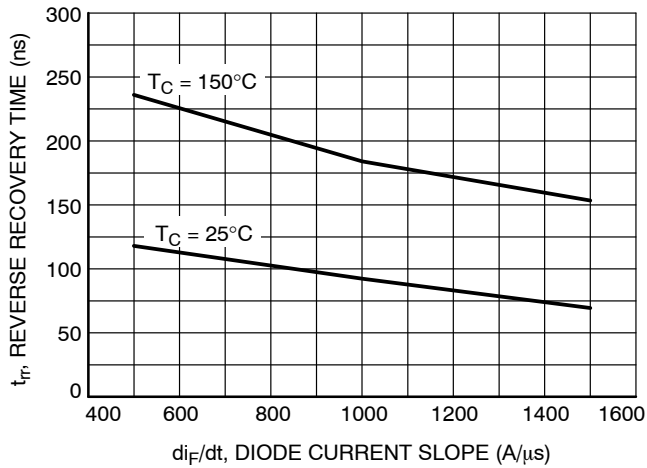


Figure 17. Reverse Recovery Time

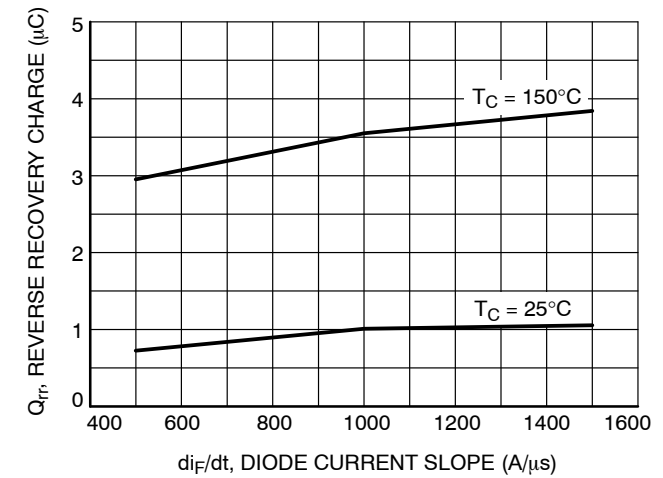


Figure 18. Stored Charge

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## TYPICAL CHARACTERISTICS

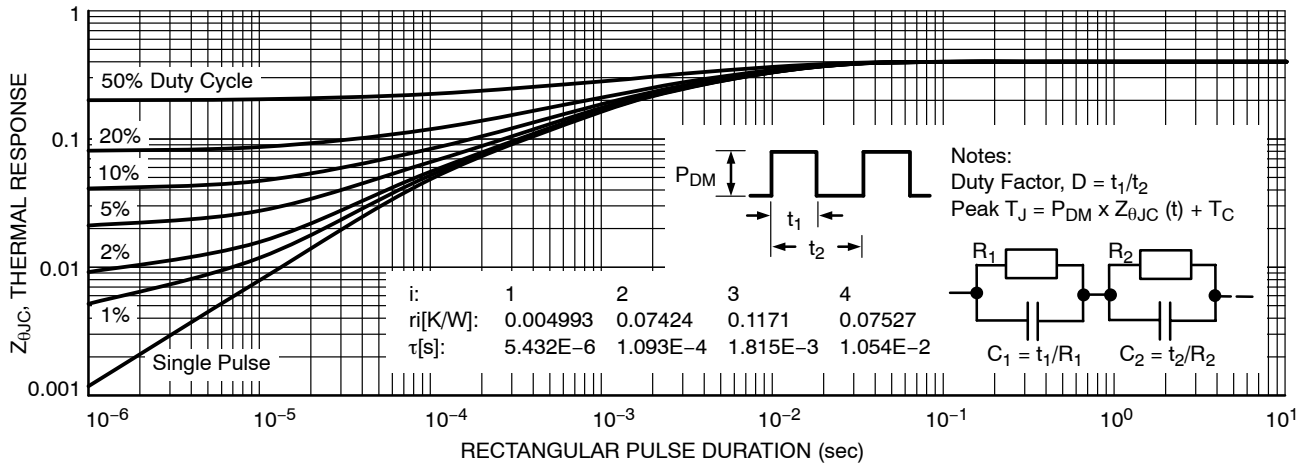


Figure 19. Transient Thermal Impedance of IGBT

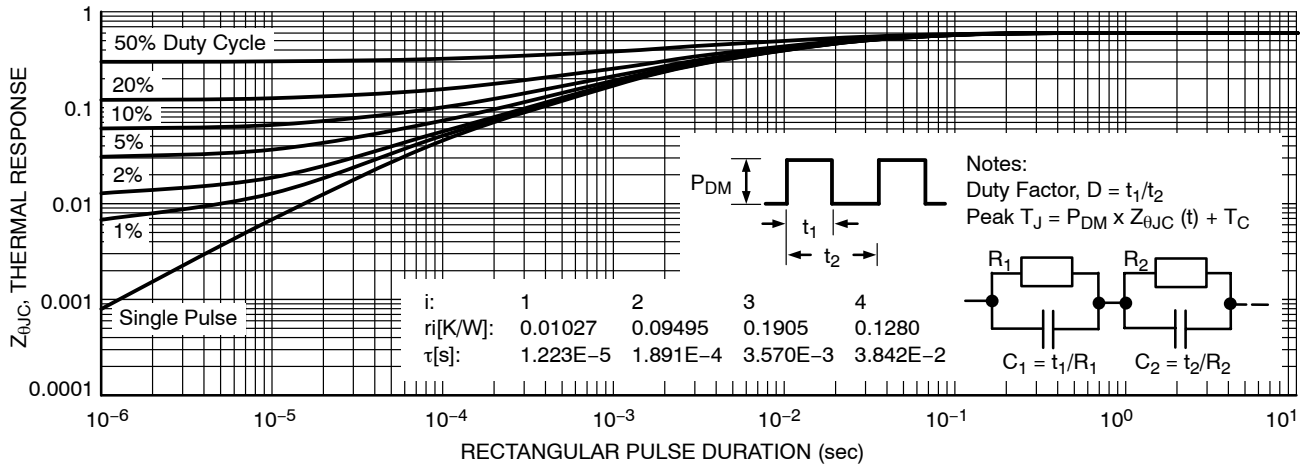
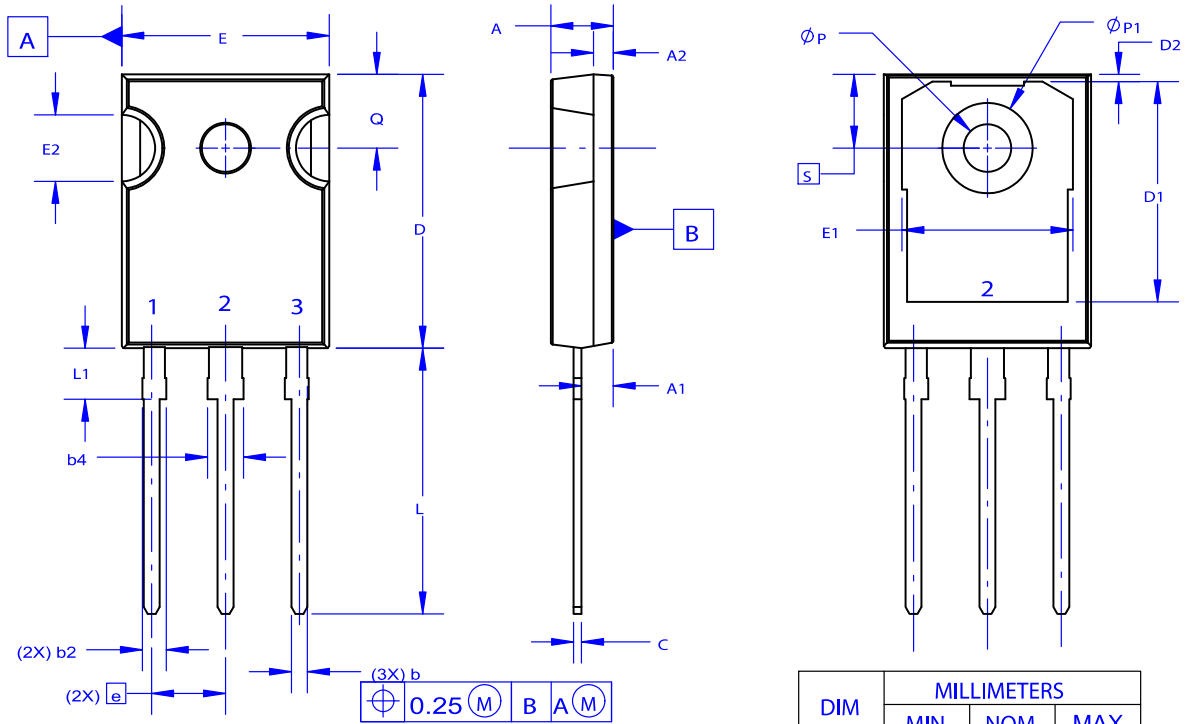


Figure 20. Transient Thermal Impedance of Diode

# FGHL75T65MQDT

## PACKAGE DIMENSIONS

TO-247-3LD  
CASE 340CX  
ISSUE A



NOTES: UNLESS OTHERWISE SPECIFIED.

- A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5 - 2009.
- D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
- E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	4.58	4.70	4.82
A1	2.20	2.40	2.60
A2	1.40	1.50	1.60
D	20.32	20.57	20.82
E	15.37	15.62	15.87
E2	4.96	5.08	5.20
e	~	5.56	~
L	19.75	20.00	20.25
L1	3.69	3.81	3.93
$\phi P$	3.51	3.58	3.65
Q	5.34	5.46	5.58
S	5.34	5.46	5.58
b	1.17	1.26	1.35
b2	1.53	1.65	1.77
b4	2.42	2.54	2.66
c	0.51	0.61	0.71
D1	13.08	~	~
D2	0.51	0.93	1.35
E1	12.81	~	~
$\phi P1$	6.60	6.80	7.00